

Radiation Hardened 2.5V Reference

The Star*Power Radiation Hardened IS-1009RH is a 2.5V shunt regulator diode designed to provide a stable 2.5V reference over a wide current range.

The device is designed to maintain stability over the full military temperature range and over time. The 0.2% reference tolerance is achieved by on-chip trimming.

An adjustment terminal is provided to allow for the calibration of system errors. The use of this terminal to adjust the reference voltage does not effect the temperature coefficient.

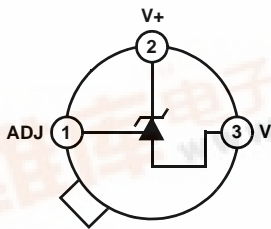
Constructed with the Intersil dielectrically isolated EBHF process, these devices are immune to Single Event Latch-up and have been specifically designed to provide highly reliable performance in harsh radiation environments.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

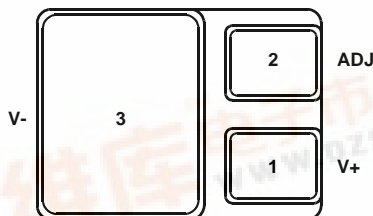
Detailed Electrical Specifications for these devices are contained in SMD 5962-00523.

Pinouts

IS2-1009RH (TO-206AB CAN)
BOTTOM VIEW



ISYE-1009RH (SMD.5)
BOTTOM VIEW



Features

- Electrically Screened to SMD # 5962-00523
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Environment
 - Total Dose 300 krad(Si) (Max)
 - Latch-up Immune Dielectrically Isolated
- Reverse Breakdown Voltage (V_Z) 2.5V
- Change in V_Z vs. Current (400 μ A to 10mA) 6mV
- Change in V_Z vs. Temp (-55°C to 125°C) 15mV
- Max Reverse Breakdown Current 20mA
- Device is tested with 10 μ F shunt capacitance connected from V_+ to V_- , which provides optimum stability
- Interchangeable with 1009 and 136 Industry Types

Applications

- Power Supply Monitoring
- Reference for 5V Systems
- A/D and D/A Reference

Ordering Information

ORDERING NUMBER	INTERNAL MKT. NUMBER	PART MARKING	TEMP. RANGE (°C)
5962F0052301VXC	IS2-1009RH-Q	F00523V	-55 to 125
5962F0052301QXC	IS2-1009RH-8	F00523 01QXC Q	-55 to 125
5962F0052301VYC	ISYE-1009RH-Q	Q 5962F00 52301VYC	-55 to 125
5962F0052301QYC	ISYE-1009RH-8	Q 5962F00 52301QYC	-55 to 125
IS2-1009RH/Proto	IS2-1009RH/Proto	IS2-1009RH/Proto	-55 to 125
ISYE-1009RH/Proto	ISYE-1009RH/Proto	ISLYE-1009RH/Proto	-55 to 125



IS-1009RH

Die Characteristics

DIE DIMENSIONS

1270 μ m x 1778 μ m (50 mils x 70 mils)
Thickness: 483 μ m \pm 25.4 μ m (19 mils \pm 1 mil)

INTERFACE MATERIALS

Glassivation

Type: Nitride (Si₃N₄) over Silox (SiO₂)
Nitride Thickness: 4.0k Å \pm 1.0k Å
Silox Thickness: 12.0k Å \pm 4.0k Å

Top Metallization

Type: AlSiCu
Thickness: 16.0k Å \pm 2k Å

Substrate

EBHF, Dielectric Isolation

Backside Finish

Silicon

ASSEMBLY RELATED INFORMATION

Substrate Potential

Unbiased (DI)

ADDITIONAL INFORMATION

Worst Case Current Density

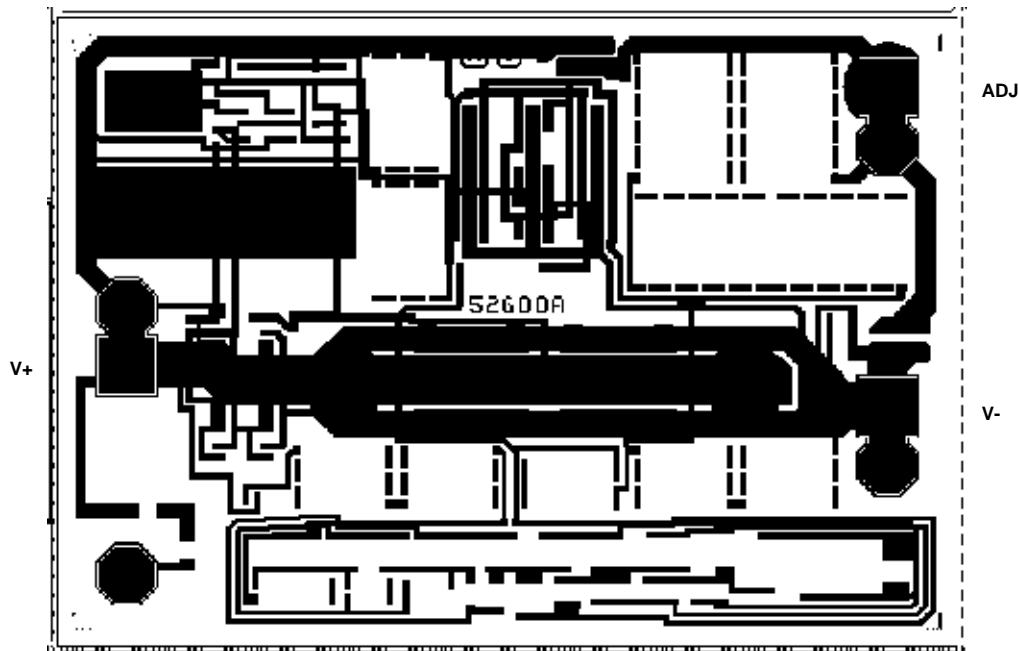
$<1.0 \times 10^5 \text{ A/cm}^2$

Transistor Count

26

Metallization Mask Layout

IS-1009RH



All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9000 quality systems.
Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design, software and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see www.intersil.com